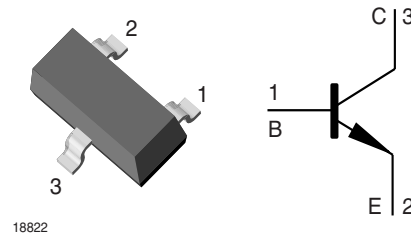


Small Signal Transistor (NPN)

Features

- NPN Silicon Epitaxial Planar Transistors
- Suited for low level, general purpose applications.
- Low current, low voltage.
- As complementary types, BCW69 and BCW70 PNP transistors are recommended.



Mechanical Data

Case: SOT-23 Plastic case

Weight: approx. 8.8 mg

Marking:

BCW71 = K1

BCW71 = K2

Packaging Codes/Options:

GS18 / 10 k per 13" reel (8 mm tape), 10 k/box

GS08 / 3 k per 7" reel (8 mm tape), 15 k/box

Pinning:

1 = Base, 2 = Emitter, 3 = Collector

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Collector - base voltage		V_{CBO}	50	V
Collector - emitter voltage		V_{CEO}	45	V
Emitter - base voltage		V_{EBO}	5.0	V
Collector current		I_C	100	mA
Collector peak current		I_{CM}	200	mA
Peak base current		I_{BM}	200	mA
Power dissipation		P_{tot}	250	mW

Maximum Thermal Resistance

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air		$R_{\theta JA}$	500 ¹⁾	$^{\circ}\text{C}/\text{W}$
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature range		T_S	- 65 to + 150	$^{\circ}\text{C}$

¹⁾ Mounted on FR-4 printed-circuit board.

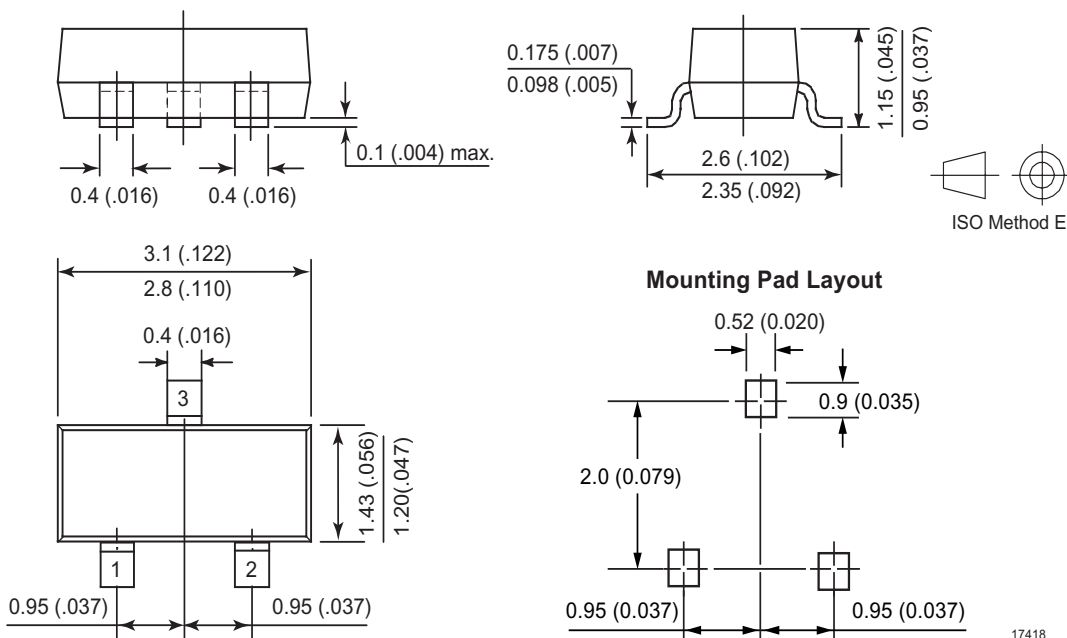
Electrical DC Characteristics

Parameter	Test condition	Part	Symbol	Min	Typ	Max	Unit
DC current gain	$V_{CE} = 5\text{ V}, I_C = 10\ \mu\text{A}$	BCW71	h_{FE}		90		
		BCW72	h_{FE}		150		
	$V_{CE} = 5\text{ V}, I_C = 2\text{ mA}$	BCW71	h_{FE}	110		220	
		BCW72	h_{FE}	200		450	
Collector - emitter saturation voltage	$I_C = 10\text{ mA}, I_B = 0.5\text{ mA}$		V_{CEsat}		120	250	mV
	$I_C = 50\text{ mA}, I_B = 2.5\text{ mA}$		V_{CEsat}		210		mV
Base - emitter saturation voltage	$I_C = 10\text{ mA}, I_B = 0.5\text{ mA}$		V_{BEsat}		750		mV
	$I_C = 50\text{ mA}, I_B = 2.5\text{ mA}$		V_{BEsat}		850		mV
Base - emitter voltage	$V_{CE} = 5\text{ V}, I_C = 2\text{ mA}$		V_{BE}	550		700	mV
Collector-base cut-off current	$V_{CB} = 20\text{ V}, V_{BE} = 0$		I_{CBO}			100	nA
	$V_{CB} = 20\text{ V}, V_{BE} = 0, T_A = 100\text{ }^\circ\text{C}$		I_{CBO}			10	μA

Electrical AC Characteristics

Parameter	Test condition	Symbol	Min	Typ	Max	Unit
Gain - bandwidth product	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}, f = 100\text{ MHz}$	f_T	100			MHz
Collector - base capacitance	$V_{CB} = 10\text{ V}, f = 1\text{ MHz}, I_E = 0$	C_{CBO}		2.5		pF
Noise figure	$V_{CE} = 5\text{ V}, I_C = 200\ \mu\text{A}, R_S = 2\text{ k}\Omega, f = 1\text{ kHz}, B = 200\text{ Hz}$	F			10	dB

Package Dimensions in mm (Inches)





Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design
and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany
Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423